

[查询"MMBS5062"供应商](#)

T-25-11

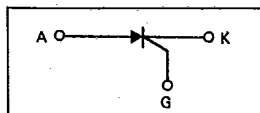
**MMBS5060
MMBS5061
MMBS5062**

Silicon Controlled Rectifiers

MAXIMUM RATINGS

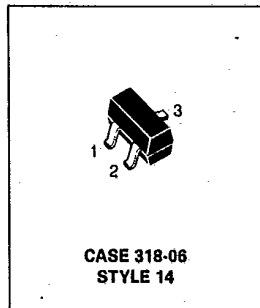
Rating	Symbol	Value	Unit
Forward Current Avg. (T _C = +67°C)	I _F	510	mA
Peak Forward Gate Voltage	V _{GFM}	5	V
Peak Forward Blocking Voltage RG = 1 k	V _{FXM}	30 60 100	V

SCRs
30 thru 100 VOLTS



THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Total Device Dissipation FR-5 Board,* T _A = 25°C Derate above 25°C	P _D	225 1.8	mW mW/°C
Thermal Resistance Junction to Ambient	R _{θJA}	556	°C/mW
Total Device Dissipation Alumina Substrate,** T _A = 25°C Derate above 25°C	P _D	300 2.4	mW mW/°C
Thermal Resistance Junction to Ambient	R _{θJA}	417	°C/mW
Junction and Storage Temperature	T _J , T _{stg}	150	°C



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*FR-5 = 1 x 0.75 x 0.62 in.
**Alumina = 0.4 x 0.3 x 0.024 in. 99.5% alumina.

ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted.)

Characteristic	Symbol	Min	Max	Unit
OFF CHARACTERISTICS				
Gate Trigger Voltage (R _L = 100 Ω, R _{GC} = 1 kΩ, T _C = 125°C)	V _{GNT}	0.1	—	V
Peak Forward Blocking Current (R _{GC} = 1 kΩ, T _C = 125°C)	I _{FXM}	—	50	μA
Peak Reverse Blocking Current (R _{GC} = 1 kΩ, T _C = 125°C)	I _{RXM}	—	50	μA
Forward Voltage* (I _F = 1.2 A Peak)	V _F	—	1.7	V
Gate Trigger Current** (R _{GC} = 1 kΩ, V _{AC} = 7 V, R _L = 100 Ω)	I _{GT}	—	200	μA
Gate Trigger Voltage (R _{GC} = 1 kΩ, V _{AC} = 7 V, R _L = 100 Ω)	V _{GT}	—	0.8	V
Holding Current (V _{AC} = 7 V, R _{GC} = 1 kΩ)	I _H	—	5	mA

*PW ≤ 1 ms, D.C. ≤ 1%.
**R_{GC} current not included in measurement.